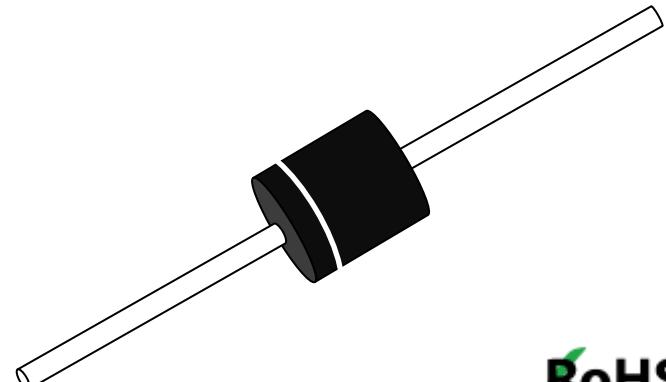
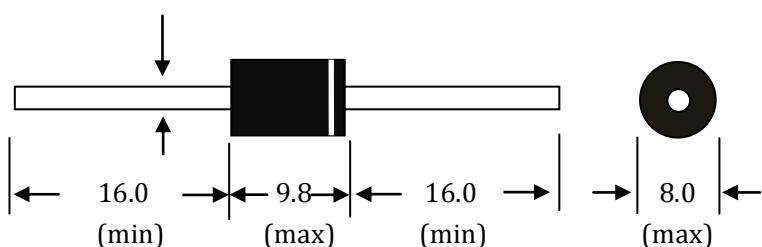


Introduce:	Reference Shape:
HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.	
Features: Avalanche characteristic. High current, low forward voltage. High frequency, Fast recovery. Conform to RoHS and SGS. Epoxy resin molded in vacuumHave anticorrosion in the surface.	

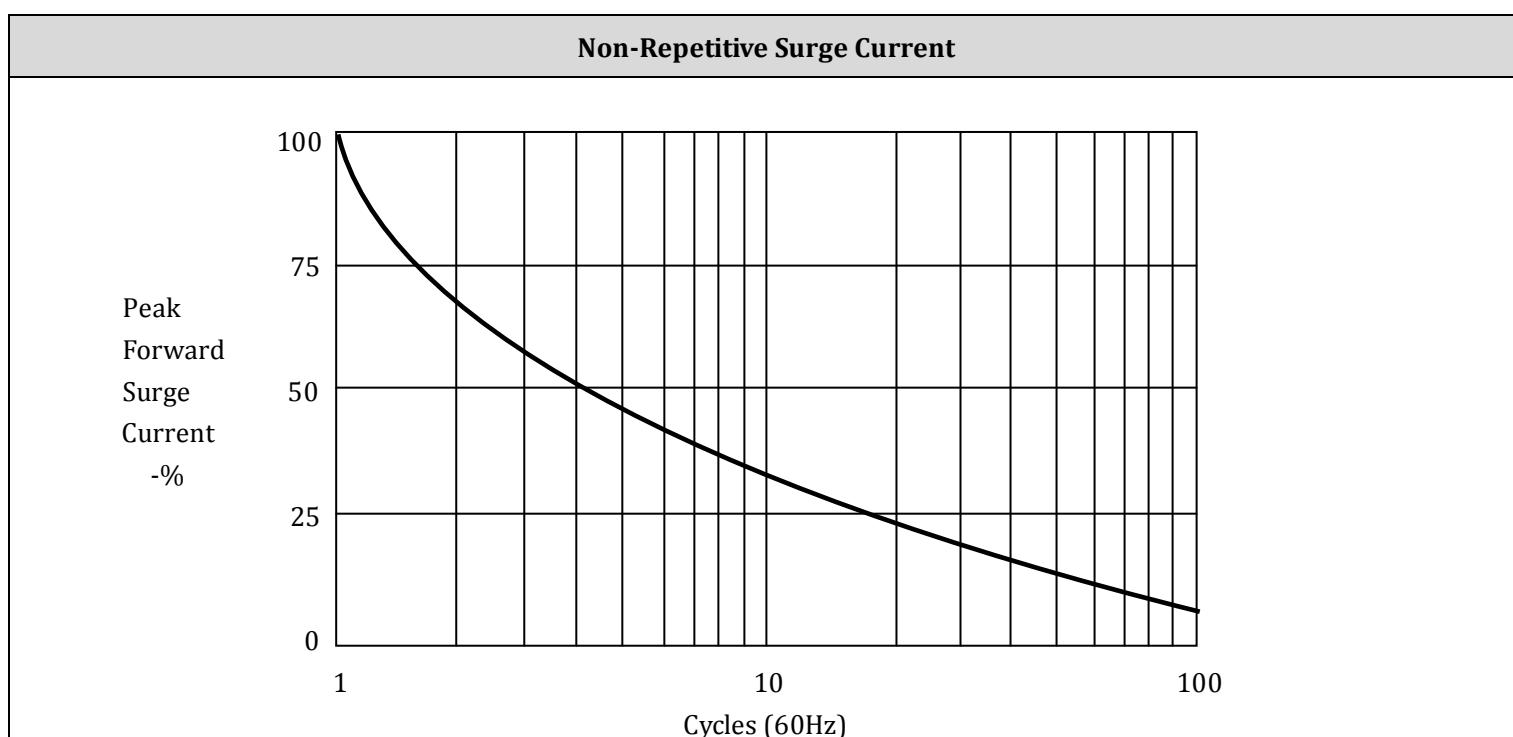
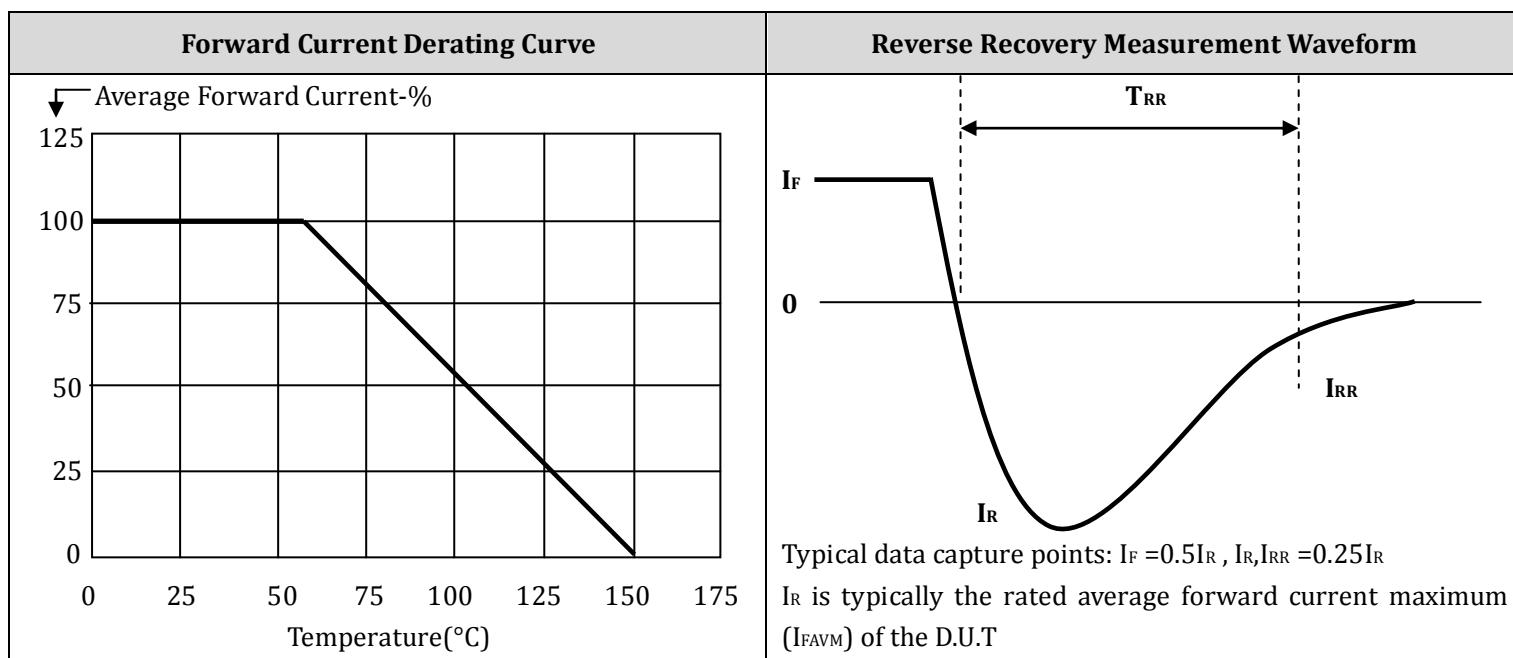
Applications:	HVGT Name:	Unit: (mm)
High pressure industrial detection. Voltage doubling circuit. High voltage rectifier. X-ray power supply.	DO-810 Lead Diameter 2.0 ± 0.05	
Mechanical Data: Case: epoxy resin molding. Terminal: welding axis. Net weight: 2.35 grams (approx).		

Maximum Ratings And Characteristics: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_A=25^\circ C$	10	kV
Non-Repetitive Peak Reverse Voltage	V_{RSM}	$T_A=25^\circ C$	12	kV
Average Forward Current Maximum	I_{FAVM}	$T_A=55^\circ C$	1.5	A
		$T_{OL}=55^\circ C$	2.2	A
Non-Repetitive Forward Surge Current	I_{FSM}	$T_A=25^\circ C$; 60Hz Half-Sine Wave; 8.3mS	30	A
Junction Temperature	T_J		150	$^\circ C$
Allowable Operation Case Temperature	T_c		-40~+150	$^\circ C$
Storage Temperature	T_{STG}		-40~+150	$^\circ C$

Electrical Characteristics: $T_A=25^\circ C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_{FM}	at $25^\circ C$; at I_{FAVM}	16.0	V
Maximum Reverse Current	I_{R1}	at $25^\circ C$; at V_{RRM}	2.0	uA
	I_{R2}	at $100^\circ C$; at V_{RRM}	20	uA
Maximum Reverse Recovery Time	T_{RR}	$I_F=200mA$; $I_R=400mA$; $I_{RR}=100mA$	80	nS
Junction Capacitance	C_J	at $25^\circ C$; $V_R=0V$; $f=1MHz$	--	pF



Marking	Type	Code	Cathode Mark
	GH3A-10K	HVGT GH3A-10K	

Packaging Standard		
Bulk Packaging	Label part number nothing "TR"	Package standard download link:
--	--	http://www.hvgtsemi.com/news/746.html